

MOSFET
OptiMOS™ 5 Linear FET 2, 100 V

Features

- Ideal for hot-swap, battery protection and e-fuse applications
- Ideal for current sharing
- Low on-resistance $R_{DS(on)}$
- Wide safe operating area SOA
- Tight $V_{GS(th)}$ spread
- Low transconductance gfs
- N-channel, normal level
- 100% avalanche tested
- Pb-free lead plating; RoHS compliant
- Halogen-free according to IEC61249-2-21

Product validation

Qualified for industrial applications according to the relevant tests of JEDEC JESD47, JESD22 and J-STD-020.

Table 1 Key performance parameters

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(on),max}$	2.3	mΩ
I_D	243	A
I_{pulse} ($V_{DS}=56\text{ V}$, $t_p=10\text{ ms}$)	5.5	A

Part number	Package	Marking	Related links
IPT023N10NM5LF2	PG-HSOF-8	23N10LF2	-

TOLL

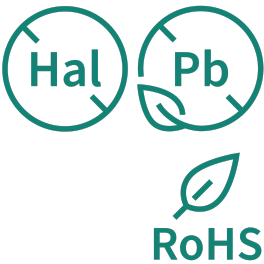
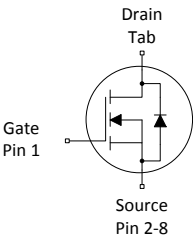
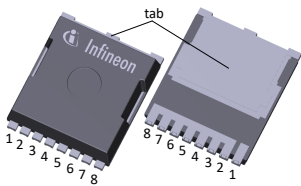




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1 Maximum ratings

at $T_A=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	243	A	$V_{GS}=10\text{ V}, T_C=25\text{ °C}$
				172		$V_{GS}=10\text{ V}, T_C=100\text{ °C}$
				180		$V_{GS}=15\text{ V}, T_C=100\text{ °C}$
				27		$V_{GS}=10\text{ V}, T_A=25\text{ °C}, R_{thJA}=40\text{ °C/W}^{2)}$
Pulsed drain current ³⁾	$I_{D,pulse}$	-	-	972	A	$T_A=25\text{ °C}$
Avalanche energy, single pulse ⁴⁾	E_{AS}	-	-	557	mJ	$I_D=100\text{ A}, R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	300	W	$T_C=25\text{ °C}$
				3.8		$T_A=25\text{ °C}, R_{thJA}=40\text{ °C/W}^{2)}$
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	-

¹⁾ Rating refers to the product only with datasheet specified absolute maximum values, maintaining case temperature as specified. For other case temperatures please refer to Diagram 2. De-rating will be required based on the actual environmental conditions.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

³⁾ See Diagrams 3 and 4 for more detailed information

⁴⁾ See Diagram 14 for more detailed information

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.5	°C/W	-
Thermal resistance, junction - ambient, 6 cm ² cooling area ⁵⁾	R_{thJA}			40		
Thermal resistance, junction - ambient, minimal footprint	R_{thJA}			62		

⁵⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	100	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2.75	3.1	3.45	V	$V_{DS}=V_{GS}$, $I_D=193\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1	1	μA	$V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$
			10	100		$V_{DS}=100\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	10	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	1.6	2.1	m Ω	$V_{GS}=15\text{ V}$, $I_D=100\text{ A}$
			2.0	2.3		$V_{GS}=10\text{ V}$, $I_D=100\text{ A}$
Gate resistance	R_G	-	1.2	1.8	Ω	-
Transconductance	g_{fs}	55	110	-	S	$ V_{DS} \geq 2 I_D R_{DS(on)max}$, $I_D=100\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Input capacitance ⁶⁾	C_{iss}	-	9100	12000	pF	$V_{GS}=0\text{ V}$, $V_{DS}=50\text{ V}$, $f=1\text{ MHz}$
Output capacitance ⁶⁾	C_{oss}		1300	1700		
Reverse transfer capacitance ⁶⁾	C_{rss}		26	46		
Turn-on delay time	$t_{d(on)}$	-	23	-	ns	$V_{DD}=50\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=100\text{ A}$, $R_{G,ext}=1.6\text{ }\Omega$
Rise time	t_r		15			
Turn-off delay time	$t_{d(off)}$		31			
Fall time	t_f		12			

⁶⁾ Defined by design. Not subject to production test.

Table 6 Gate charge characteristics ⁷⁾

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	61	-	nC	$V_{DD}=50\text{ V}$, $I_D=100\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge at threshold	$Q_{g(th)}$		28	-	nC	
Gate to drain charge ⁸⁾	Q_{gd}		19.3	29	nC	
Switching charge	Q_{sw}		52	-	nC	
Gate charge total ⁸⁾	Q_g		115	144	nC	
Gate plateau voltage	$V_{plateau}$		6.7	-	V	
Gate charge total, sync. FET	$Q_{g(sync)}$	-	104	-	nC	$V_{DS}=0.1\text{ V}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge ⁸⁾	Q_{oss}	-	147	196	nC	$V_{DS}=50\text{ V}$, $V_{GS}=0\text{ V}$

⁷⁾ See "Gate charge waveforms" for parameter definition

⁸⁾ Defined by design. Not subject to production test.

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	243	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$			972		
Diode forward voltage	V_{SD}	-	0.86	1.2	V	$V_{GS}=0\text{ V}$, $I_F=100\text{ A}$, $T_J=25\text{ °C}$
Reverse recovery time ⁹⁾	t_{rr}	-	57	114	ns	$V_R=50\text{ V}$, $I_F=100\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge ⁹⁾	Q_{rr}		81	162	nC	

⁹⁾ Defined by design. Not subject to production test.

4 Electrical characteristics diagrams

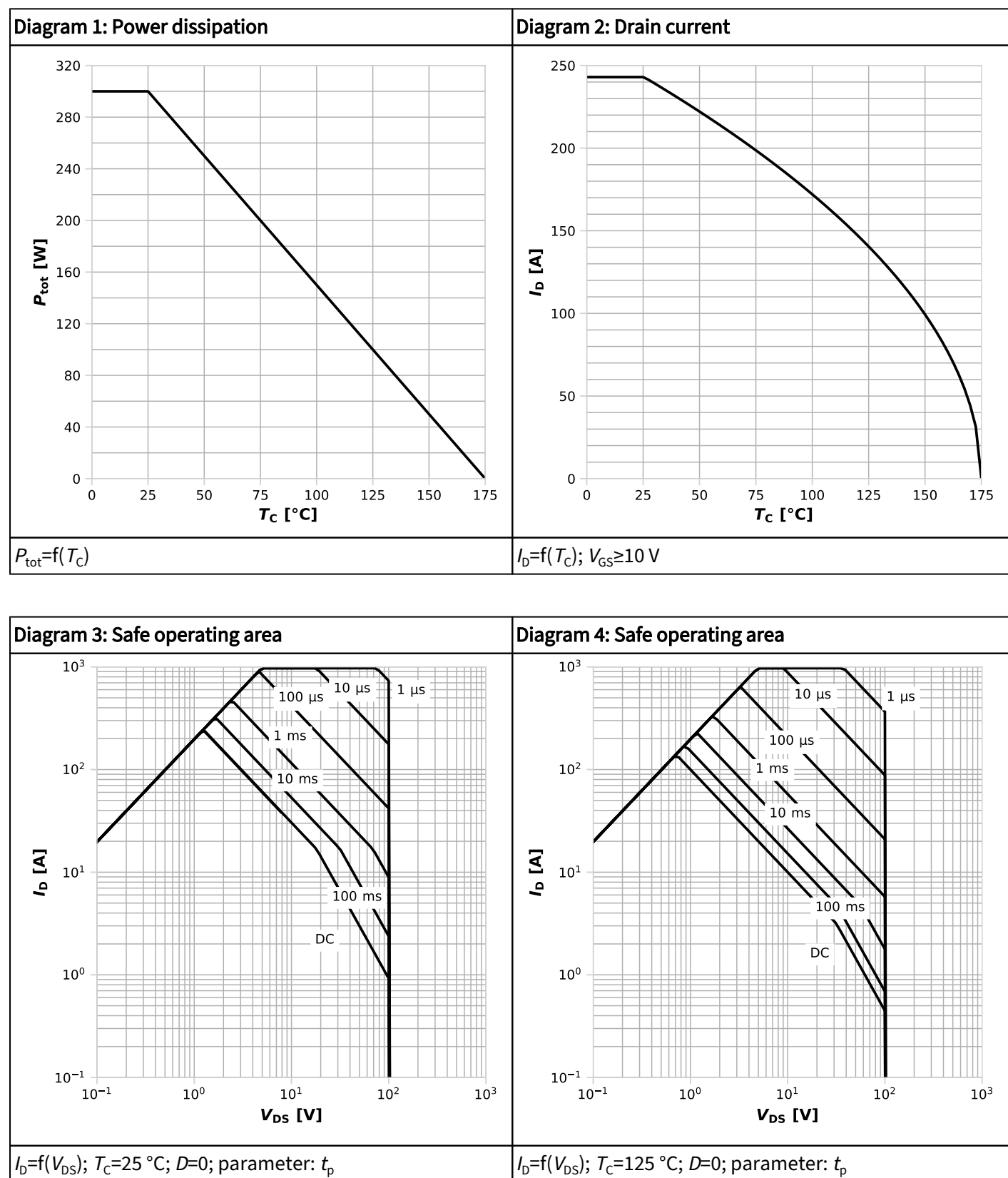
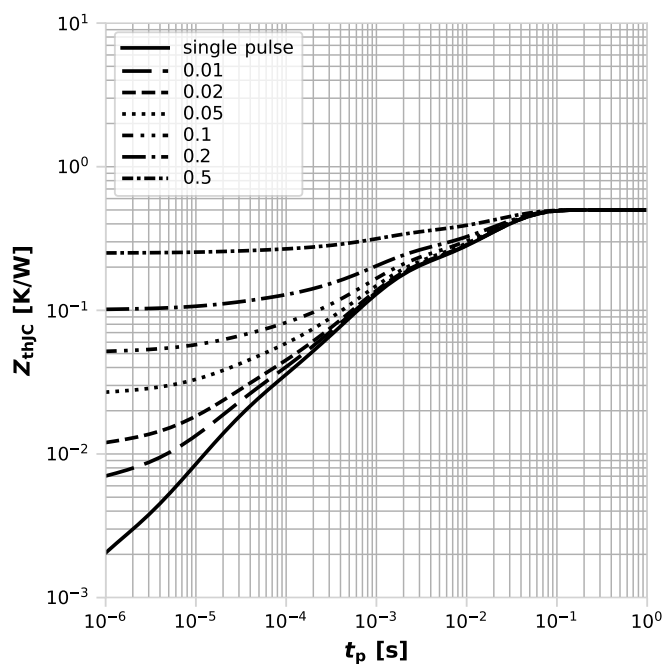
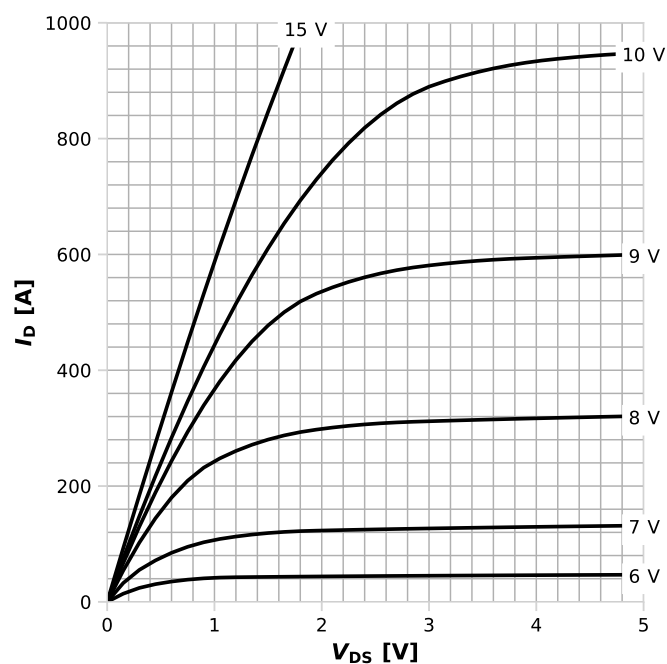


Diagram 5: Max. transient thermal impedance



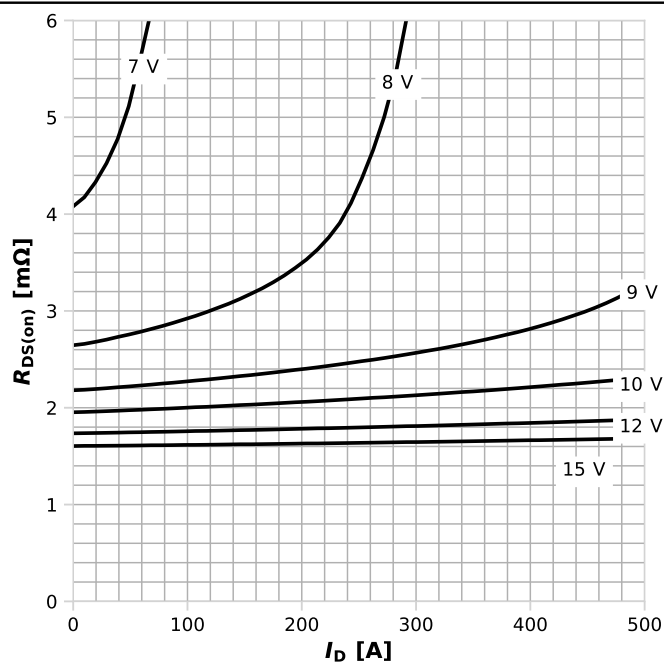
$$Z_{thJC} = f(t_p); \text{ parameter: } D = t_p / T$$

Diagram 6: Typ. output characteristics



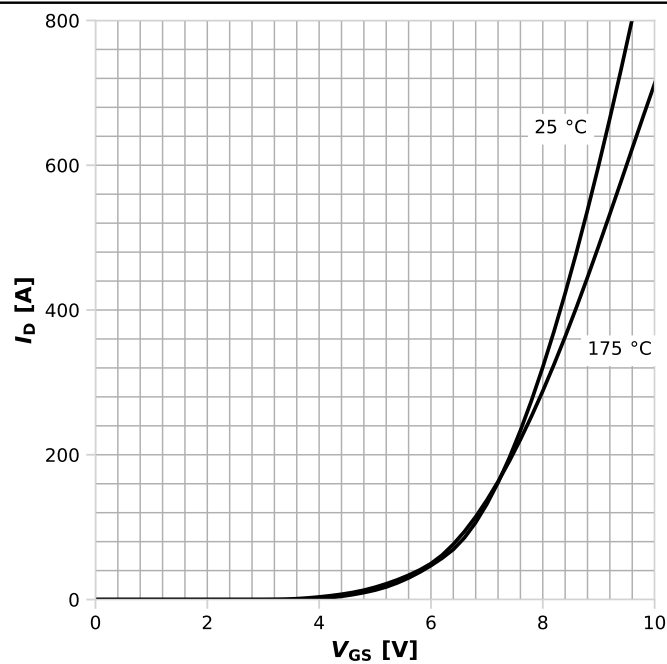
$$I_D = f(V_{DS}, T_j = 25^\circ\text{C}; \text{ parameter: } V_{GS})$$

Diagram 7: Typ. drain-source on resistance



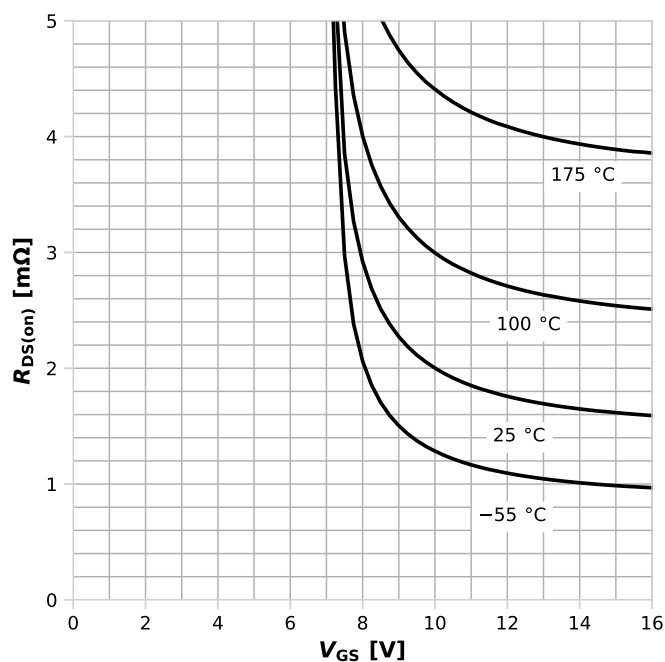
$$R_{DS(on)} = f(I_D, T_j = 25^\circ\text{C}; \text{ parameter: } V_{GS})$$

Diagram 8: Typ. transfer characteristics



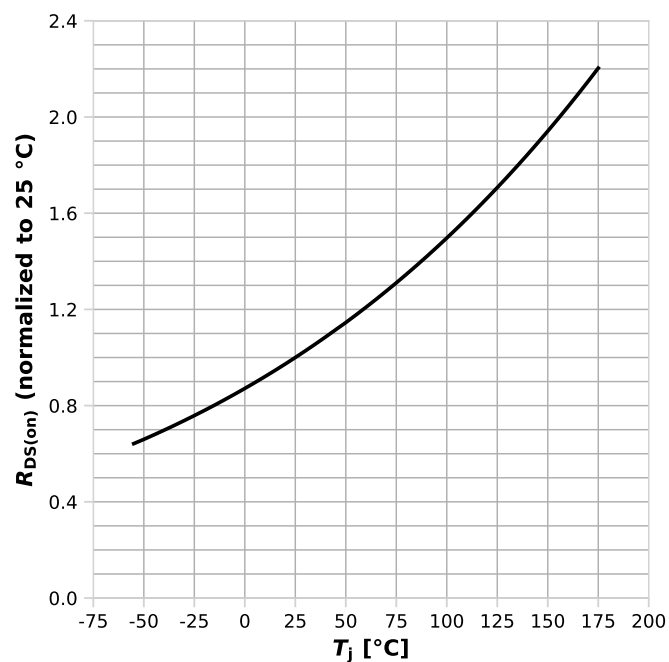
$$I_D = f(V_{GS}, |V_{DS}| > 2|I_D|R_{DS(on)max}; \text{ parameter: } T_j)$$

Diagram 9: Typ. drain-source on resistance



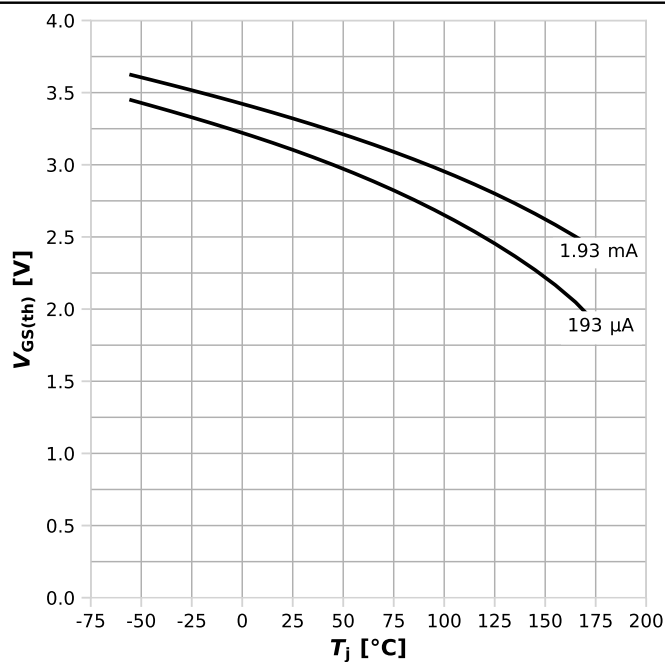
$$R_{DS(on)} = f(V_{GS}), I_D = 100 \text{ A; parameter: } T_j$$

Diagram 10: Normalized drain-source on resistance



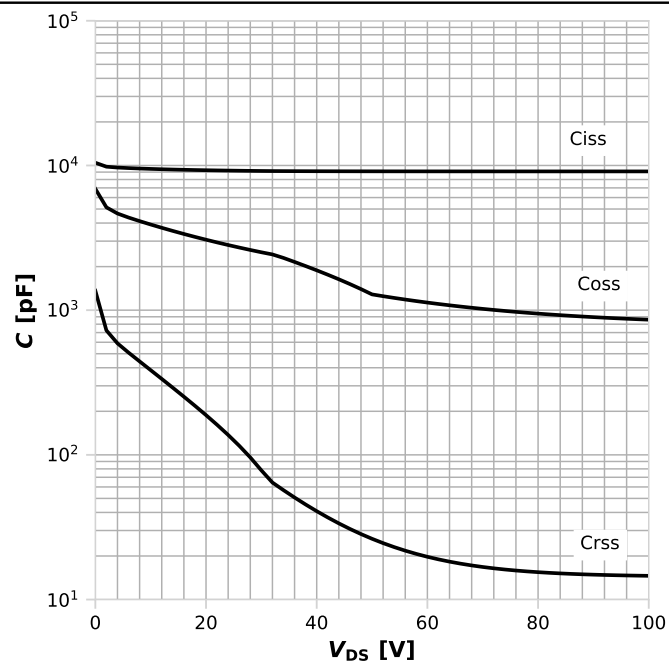
$$R_{DS(on)} = f(T_j), I_D = 100 \text{ A, } V_{GS} = 10 \text{ V}$$

Diagram 11: Typ. gate threshold voltage



$$V_{GS(th)} = f(T_j), V_{GS} = V_{DS}; \text{ parameter: } I_D$$

Diagram 12: Typ. capacitances



$$C = f(V_{DS}); V_{GS} = 0 \text{ V; } f = 1 \text{ MHz}$$

Diagram 13: Forward characteristics of reverse diode

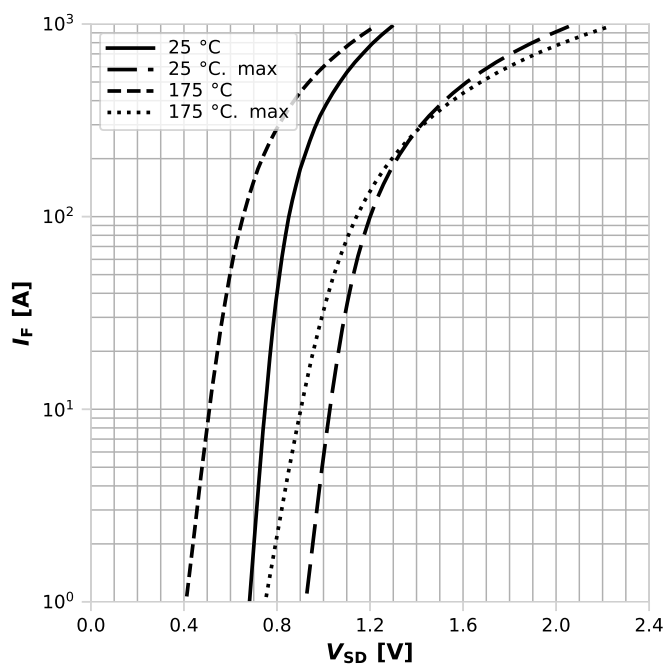

 $I_F = f(V_{SD})$; parameter: T_j

Diagram 14: Avalanche characteristics

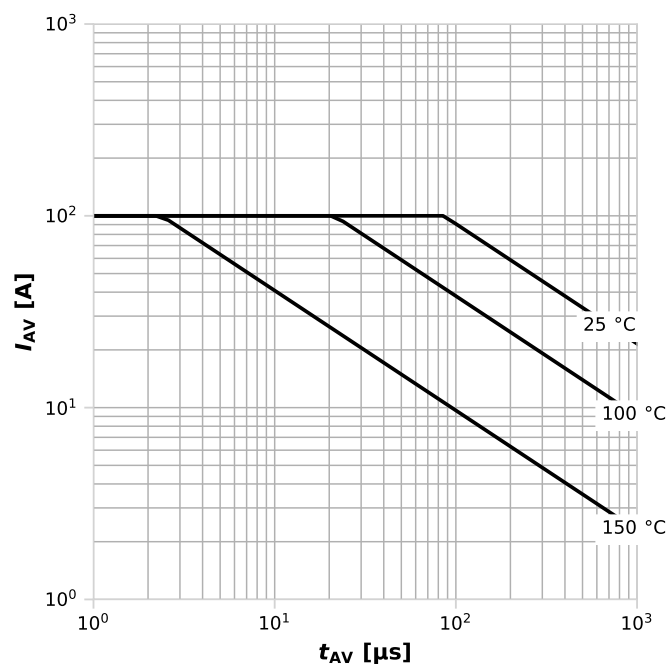

 $I_{AS} = f(t_{AV})$; $R_{GS} = 25 \Omega$; parameter: $T_{j,start}$

Diagram 15: Typ. gate charge

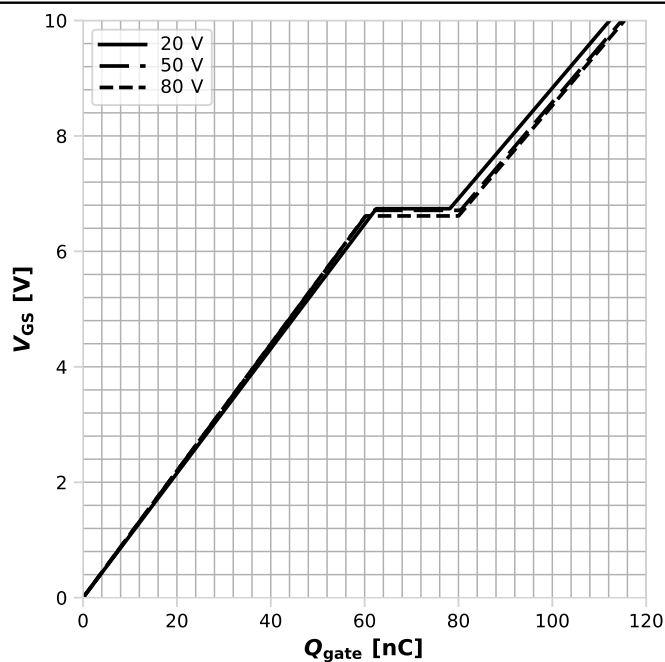
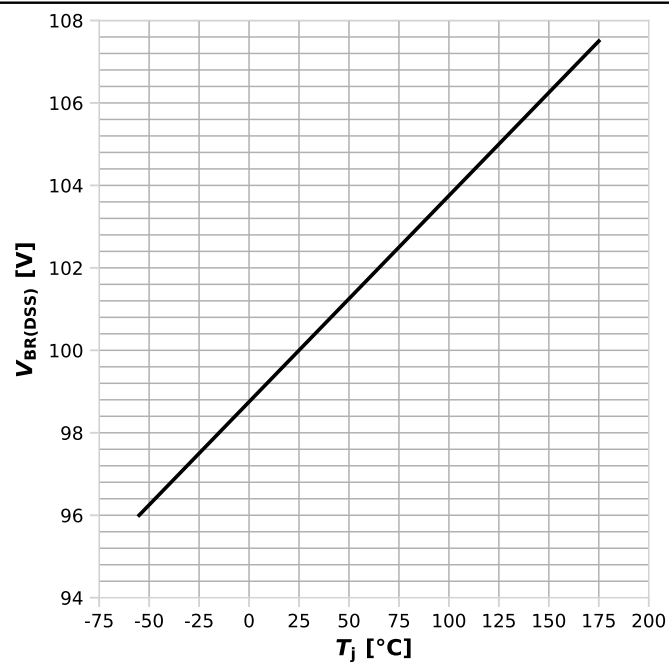
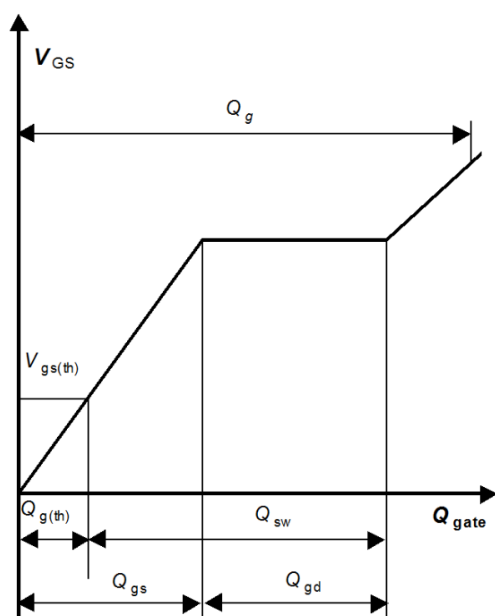

 $V_{GS} = f(Q_{gate})$, $I_D = 100 \text{ A}$ pulsed, $T_j = 25 \text{ °C}$; parameter: V_{DD}

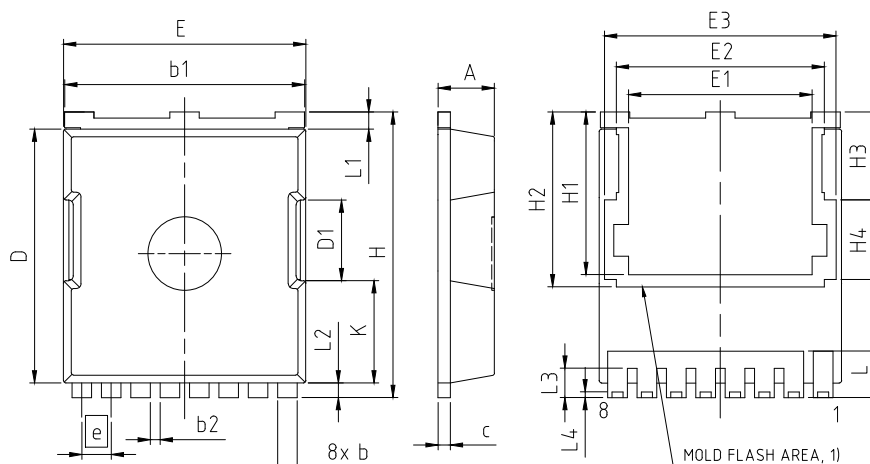
Diagram 16: Min. drain-source breakdown voltage


 $V_{BR(DSS)} = f(T_j)$; $I_D = 1 \text{ mA}$

Gate charge waveforms

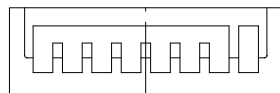


5 Package outlines



PACKAGE - GROUP NUMBER: PG-HSOF-8-U01		
DIMENSIONS	MILLIMETERS	
	MIN.	MAX.
A	2.20	2.40
b	0.70	0.90
b1	9.70	9.90
b2	0.40	---
c	0.40	0.60
D	10.28	10.58
D1	3.30	
E	9.70	10.10
E1	7.50	
E2	8.50	
E3	9.46	
e	1.20 (BSC)	
H	11.48	11.88
H1	6.55	6.95
H2	7.15	7.50
H3	3.59	
H4	3.26	
N	8	
K	4.03	4.33
L	1.60	2.10
L1	0.50	0.90
L2	0.45	0.75
L3	1.00	1.30
L4	0.13	0.33

5:1

OPTIONAL LEAD FORM:
WITHOUT LTI OPTION

1) PARTIALLY COVERED WITH MOLD FLASH

Figure 1 Outline PG-HSOF-8, dimensions in mm

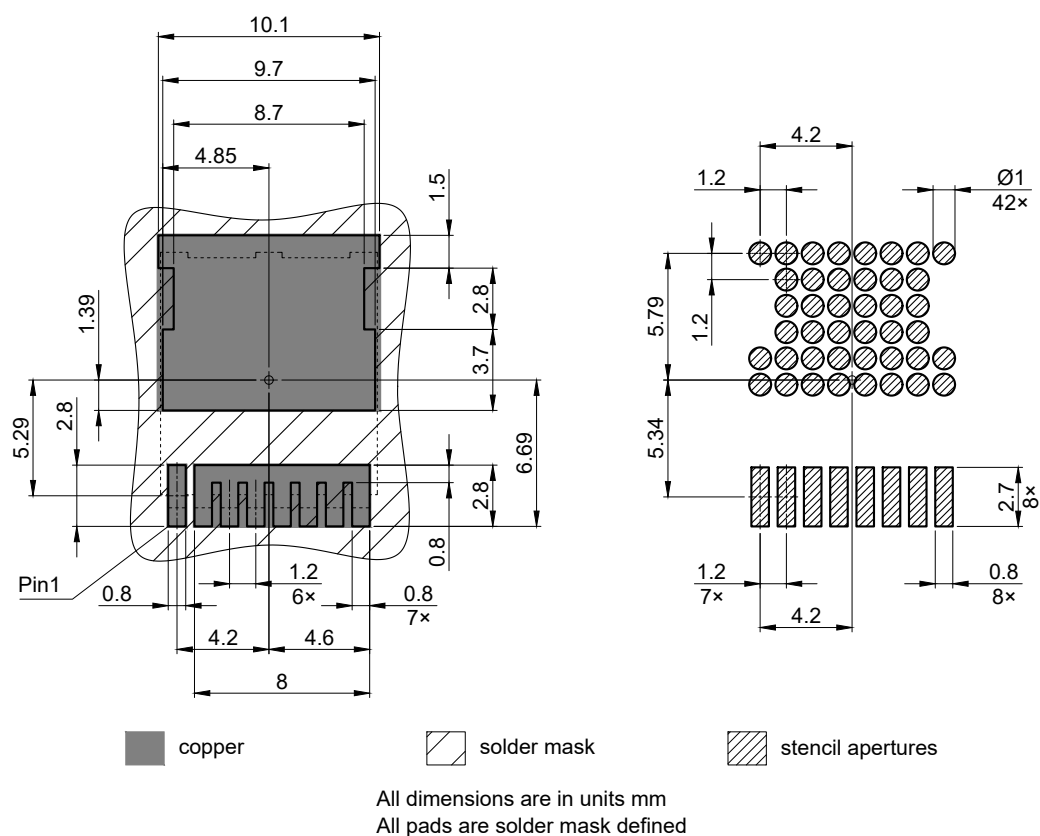
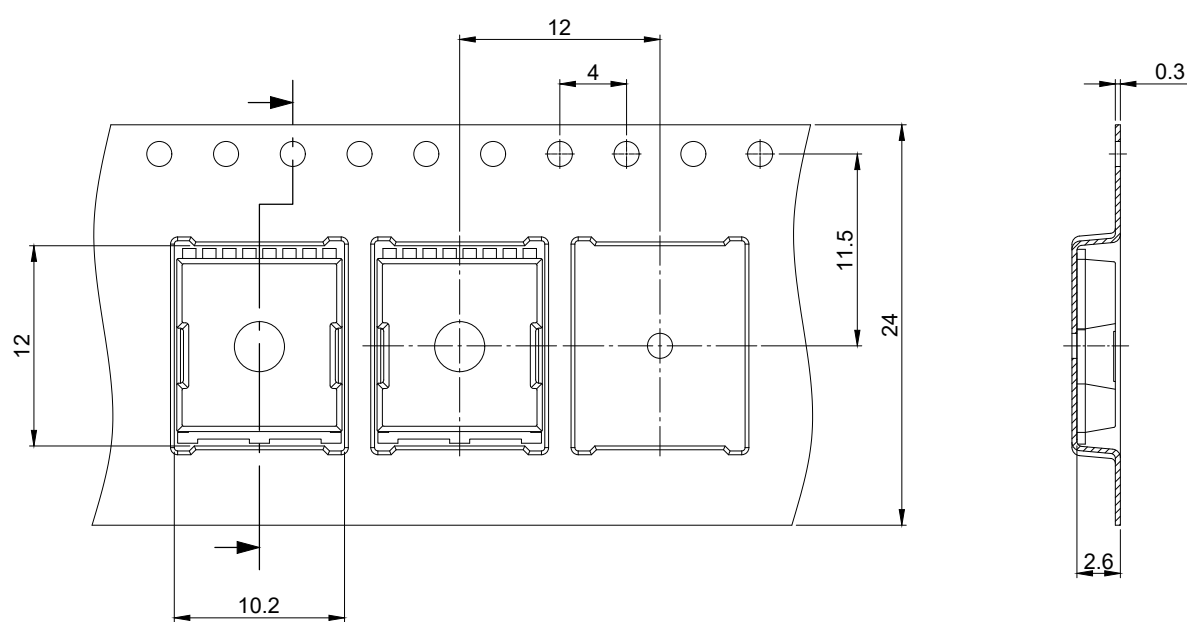


Figure 2 Footprint drawing PG-HSOF-8, dimensions in mm



All dimensions are in units mm

The drawing is in compliance with ISO 128-30, Projection Method 1 []

Figure 3 Packaging variant PG-HSOF-8, dimensions in mm



Revision history

IPT023N10NM5LF2

Revision 2025-11-04, Rev. 1.2

Previous revisions

Revision	Date	Subjects (major changes since last revision)
1.0	2024-08-22	Release of final datasheet
1.1	2025-08-28	Update gate threshold voltage
1.2	2025-11-04	Update "Features"

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